

**REMARKS**

By this amendment, no claim has been amended, cancelled or and added. Accordingly, claims 1-38 are currently pending in the application, of which claims 1, 10, 22 and 35 are independent claims. The Office Action indicates that claims 10-34 are allowed.

In view of the following Remarks, Applicant respectfully requests reconsideration and timely withdrawal of the pending rejections for the reasons discussed below.

***Rejections Under 35 U.S.C. §102***

Claims 1-9 and 35-38 stand rejected under 35 U.S.C. §102(e) as being anticipated by U. S. Patent No. 6,466,289 issued to Lee, *et al.* ("Lee"). Applicant respectfully traverses this rejection for at least the following reasons.

Independent claim 1 recites "a light interception pattern formed of *the same layer as the semiconductor pattern*". In this regard, the Examiner asserted that the light-shield strips 64 shown in FIG. 7 of Lee corresponds to the claimed light interception pattern. This assertion is respectfully disagreed with.

As described in column 5, lines 11-15 of Lee, "*A first data line 60 ... includes a first portion 66 ... and a second portion 64*". The first data line 60, a source electrode 61, a drain electrode 62 are parts of *the first data pattern*, which "may be made of one selected from chromium, aluminum, aluminum alloy, molybdenum and molybdenum alloy" (Column 3, Lines 54-55).

As shown in FIG. 3, the source electrode 61 and the drain electrode 62 are formed over a channel region 40. The channel region 40 is "made of a semiconductor such as a hydrogenated

amorphous silicon (a-si:H)" (Column 3, Lines 33-34). Thus, it is submitted that the channel region 40 corresponds to the claimed semiconductor pattern.

As described above, the second portion 64 and the channel region 40 are formed of *two different materials*. Thus, the Examiner's assertion that the second portion 64 is formed of the same layer as the channel region 40 has *no support from Lee*. Rather, that the second portion 64 is formed of the same layer as the source electrode 61 and the drain electrode 62, which are formed over a channel region 40 with the ohmic contact layer 51 and 52 therebetween.

Thus, it is submitted that, in Lee, the second portion 64 is not formed of the same layer as the channel region 40, and Lee fails to disclose or suggest the second portion 64 formed of the same layer as the channel region 40. Hence, it is respectfully submitted that claim 1 is patentable over Lee.

Independent claim 35 recites "a light interceptor made of the same layer as the semiconductor layer ...". As previously mentioned, Lee does not disclose this claimed feature, and, hence would be also patentable at least for the same reason.

For the reasons described above, it is submitted that independent claims 1 and 35 are patentable over Lee. Claims 2-9 and 36-38 that are dependent from claims 1 and 35, respectively, would be also patentable at least for the same reason. Accordingly, Applicant respectfully requests withdrawal of the rejection.

### **CONCLUSION**

Applicant believes that a full and complete response has been made to the pending Office Action and respectfully submit that all of the stated objections and grounds for rejection have

been overcome or rendered moot. Accordingly, Applicant respectfully submits that all pending claims are allowable and that the application is in condition for allowance.

Should the Examiner feel that there are any issues outstanding after consideration of this response, the Examiner is invited to contact the Applicant's undersigned representative at the number below to expedite prosecution.

Prompt and favorable consideration of this Reply is respectfully requested.

Respectfully submitted,



Hae-Chan Park  
Reg. No. 50,114

Date: October 10, 2003

**McGuireWoods LLP**  
1750 Tysons Boulevard  
Suite 1800  
McLean, VA 22102-4215  
Tel: 703-712-5365  
Fax: 703-712-5280  
HCP:WSC/kbs

\\COM\213827.1